



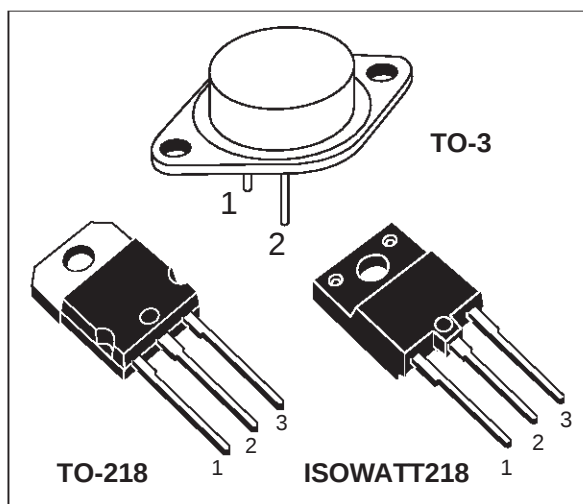
BU941/BU941P BU941PFI

HIGH VOLTAGE IGNITION COIL DRIVER NPN POWER DARLINGTON

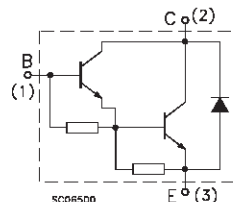
- NPN DARLINGTON
- INTEGRATED ANTIPARALLEL COLLECTOR-EMITTER DIODE
- VERY RUGGED BIPOLAR TECHNOLOGY
- HIGH OPERATING JUNCTION TEMPERATURE
- WIDE RANGE OF PACKAGES

APPLICATIONS

- HIGH RUGGEDNESS ELECTRONIC IGNITIONS



INTERNAL SCHEMATIC DIAGRAM



for TO-3
Emitter: pin 2
Base: pin1
Collector: tab

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value			Unit
		BU941	BU941P	BUB941PFI	
V_{CES}	Collector-Emitter Voltage ($V_{BE} = 0$)	500			V
V_{CEO}	Collector-Emitter Voltage ($I_B = 0$)	400			V
V_{EBO}	Emitter-Base Voltage ($I_C = 0$)	5			V
I_C	Collector Current	15			A
I_{CM}	Collector Peak Current	30			A
I_B	Base Current	1			A
I_{BM}	Base Peak Current	5			A
P_{tot}	Total Dissipation at $T_c = 25^\circ\text{C}$	180	155	65	W
T_{stg}	Storage Temperature	-65 to 200	-65 to 175	-65 to 175	$^\circ\text{C}$
T_j	Max. Operating Junction Temperature	200	175	175	$^\circ\text{C}$

THERMAL DATA

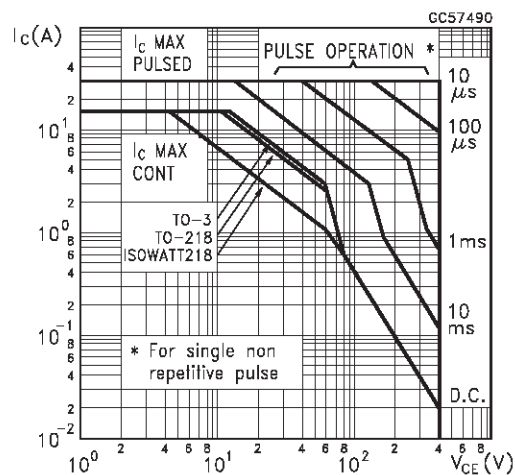
		TO-3	TO-218	ISOWATT218	
$R_{thj-case}$	Thermal Resistance Junction-case Max	0.97	0.97	2.3	$^{\circ}\text{C}/\text{W}$

ELECTRICAL CHARACTERISTICS ($T_{case} = 25^{\circ}\text{C}$ unless otherwise specified)

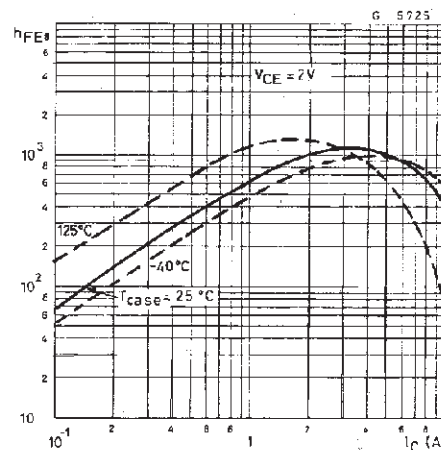
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{CES}	Collector Cut-off Current ($V_{BE} = 0$)	$V_{CE} = 500\text{ V}$ $V_{CE} = 500\text{ V}$ $T_J = 125^{\circ}\text{C}$			100 0.5	μA mA
I_{CEO}	Collector Cut-off Current ($I_B = 0$)	$V_{CE} = 450\text{ V}$ $V_{CE} = 450\text{ V}$ $T_J = 125^{\circ}\text{C}$			100 0.5	μA mA
I_{EBO}	Emitter Cut-off Current ($I_C = 0$)	$V_{EB} = 5\text{ V}$			20	mA
$V_{CEO(sus)}^*$	Collector-Emitter Sustaining Voltage ($I_B = 0$)	$I_C = 100\text{ mA}$ $L = 10\text{ mH}$ $V_{Clamp} = 400\text{ V}$ (See FIG.4)	400			V
$V_{CE(sat)}^*$	Collector-Emitter Saturation Voltage	$I_C = 8\text{ A}$ $I_B = 100\text{ mA}$ $I_C = 10\text{ A}$ $I_B = 250\text{ mA}$ $I_C = 12\text{ A}$ $I_B = 300\text{ mA}$			1.6 1.8 2	V V V
$V_{BE(sat)}^*$	Base-Emitter Saturation Voltage	$I_C = 8\text{ A}$ $I_B = 100\text{ mA}$ $I_C = 10\text{ A}$ $I_B = 250\text{ mA}$ $I_C = 12\text{ A}$ $I_B = 300\text{ mA}$			2.2 2.5 2.7	V V V
h_{FE}^*	DC Current Gain	$I_C = 5\text{ A}$ $V_{CE} = 10\text{ V}$	300			
V_F	Diode Forward Voltage	$I_F = 10\text{ A}$			2.5	V
	Functional Test (see fig. 1)	$V_{CC} = 24\text{ V}$ $V_{Clamp} = 400\text{ V}$ $L = 7\text{ mH}$	10			A
t_s t_f	INDUCTIVE LOAD Storage Time Fall Time (see fig. 3)	$V_{CC} = 12\text{ V}$ $V_{Clamp} = 300\text{ V}$ $V_{BE} = 0$ $R_{BE} = 47\ \Omega$ $L = 7\text{ mH}$ $I_C = 7\text{ A}$ $I_B = 70\text{ mA}$		15 0.5		μs μs

* Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %

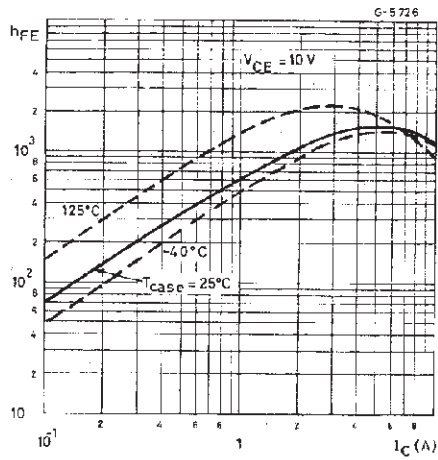
Safe Operating Area



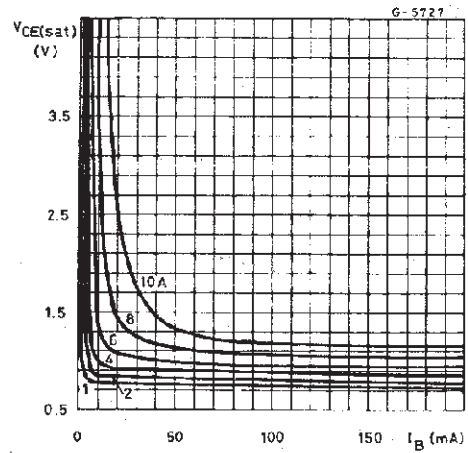
DC Current Gain



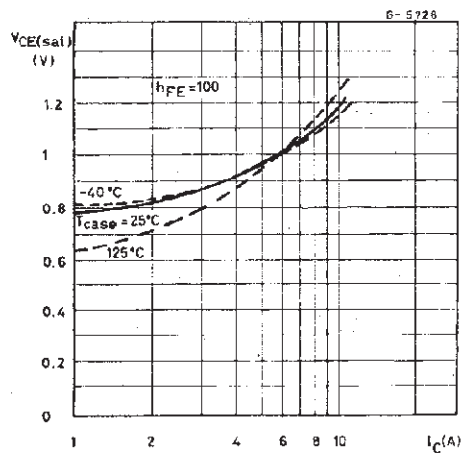
DC Current Gain



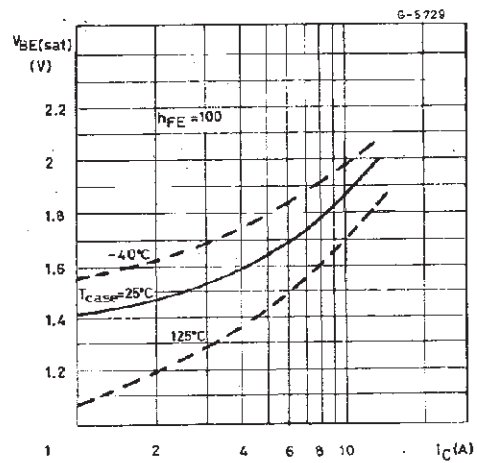
Collector-emitter Saturation Voltage



Collector-emitter Saturation Voltage



Base-emitter Saturation Voltage



Switching Time Inductive Load (see fig.3)

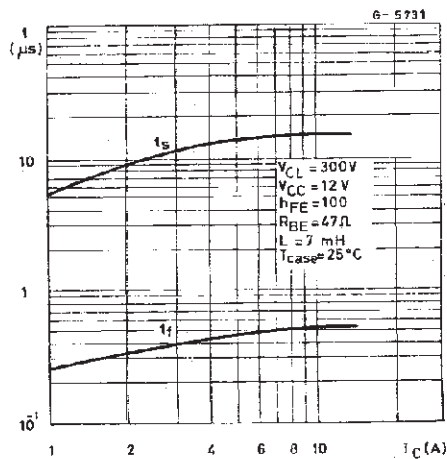


FIGURE 1: Functional Test Circuit

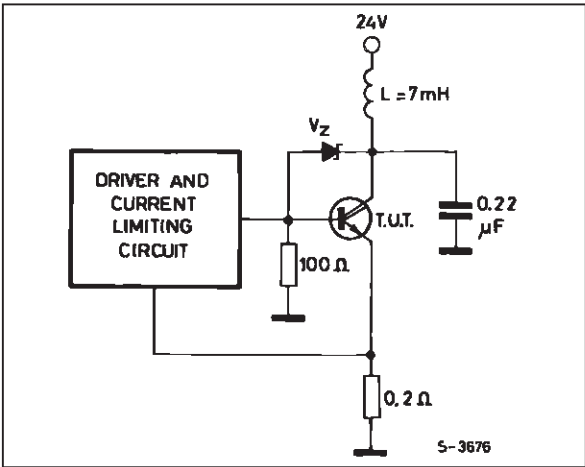


FIGURE 2: Functional Test Waveforms

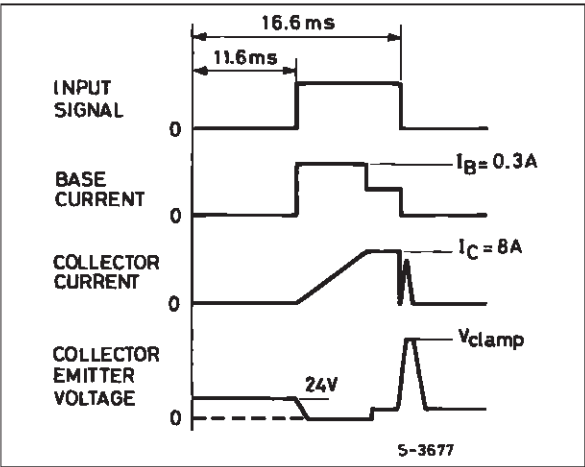


FIGURE 3: Switching Time Test Circuit

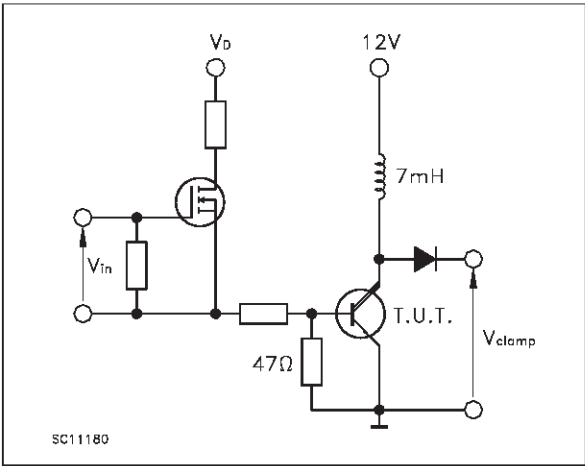
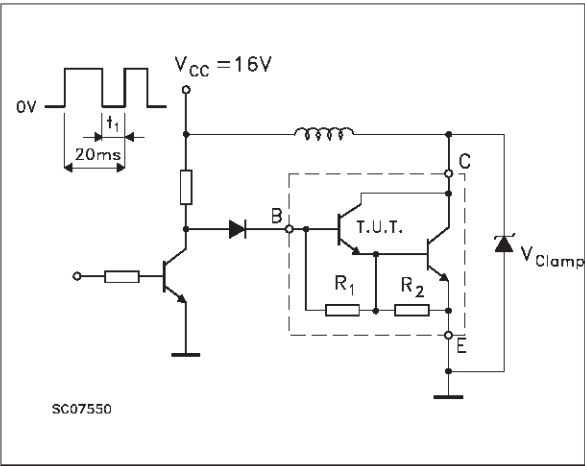
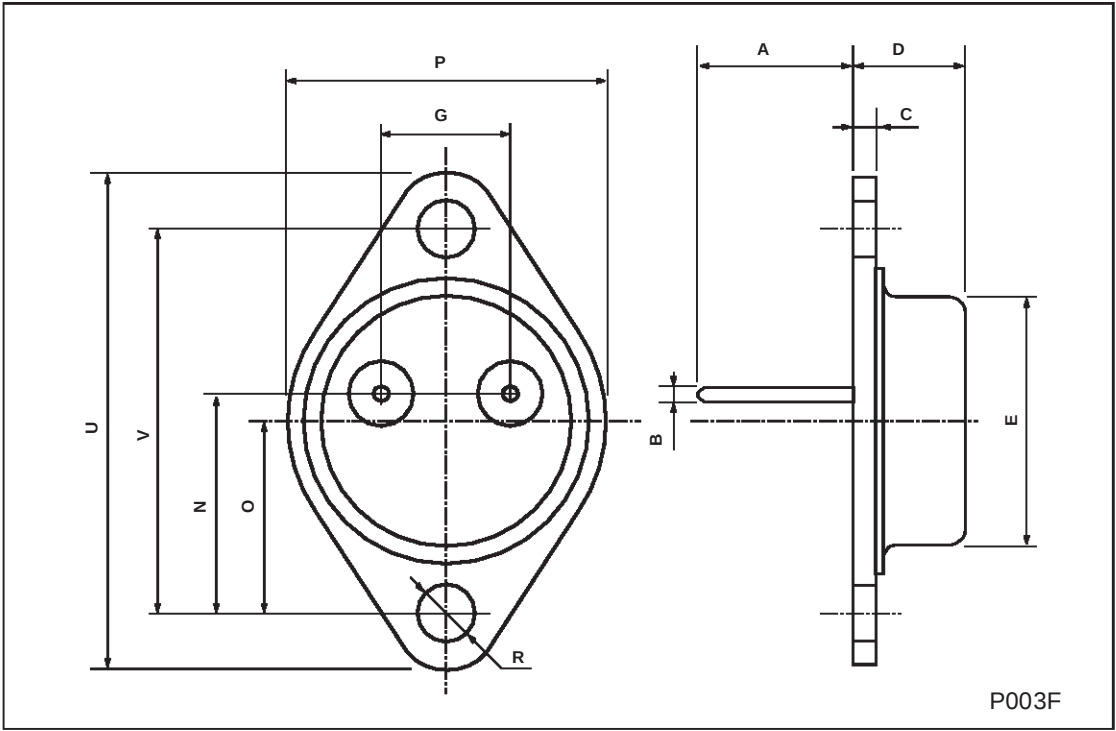


FIGURE 4: Sustaining Voltage Test Circuit



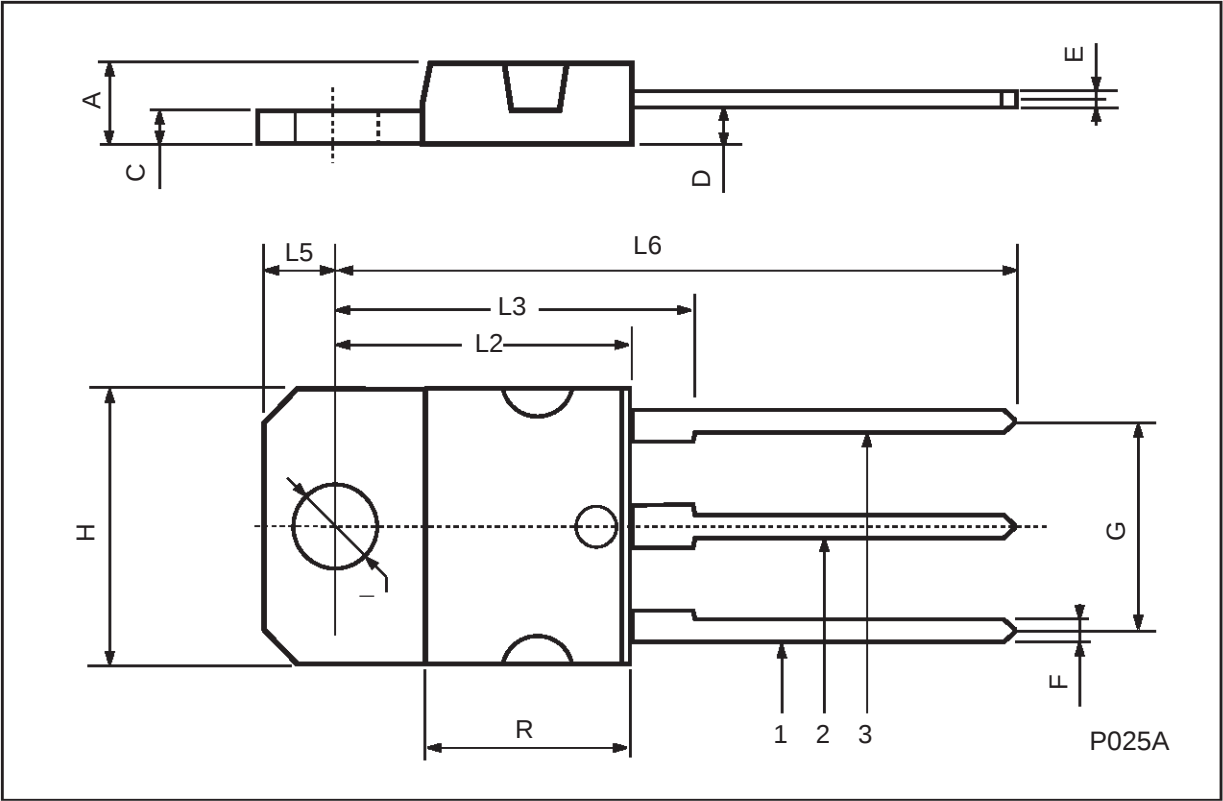
TO-3 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	11.00		13.10	0.433		0.516
B	0.97		1.15	0.038		0.045
C	1.50		1.65	0.059		0.065
D	8.32		8.92	0.327		0.351
E	19.00		20.00	0.748		0.787
G	10.70		11.10	0.421		0.437
N	16.50		17.20	0.649		0.677
P	25.00		26.00	0.984		1.023
R	4.00		4.09	0.157		0.161
U	38.50		39.30	1.515		1.547
V	30.00		30.30	1.187		1.193



TO-218 (SOT-93) MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.7		4.9	0.185		0.193
C	1.17		1.37	0.046		0.054
D		2.5			0.098	
E	0.5		0.78	0.019		0.030
F	1.1		1.3	0.043		0.051
G	10.8		11.1	0.425		0.437
H	14.7		15.2	0.578		0.598
L2	–		16.2	–		0.637
L3		18			0.708	
L5	3.95		4.15	0.155		0.163
L6		31			1.220	
R	–		12.2	–		0.480
Ø	4		4.1	0.157		0.161



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